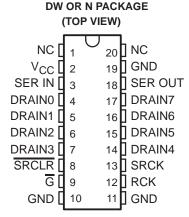
- Low r<sub>DS(on)</sub> . . . 5 Ω
- Avalanche Energy . . . 30 mJ
- Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- Enhanced Cascading for Multiple Stages
- All Registers Cleared With Single Input
- Low Power Consumption

#### description

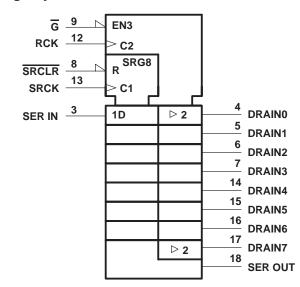
The TPIC6B596 is a monolithic, high-voltage, medium-current power 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift-register clock (SRCK) and the register clock (RCK), respectively. The storage register transfers data to the output buffer when shift-register clear ( $\overline{SRCLR}$ ) is high. When  $\overline{SRCLR}$  is low, all registers in the device are cleared. When output enable ( $\overline{G}$ ) is held high, all data in the output buffers is held low and all drain outputs are off. When  $\overline{G}$  is held low, data from the storage register is transparent to the output buffers. When data in the output buffers is low, the DMOStransistor outputs are off. When data is high, the



NC - No internal connection

#### logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

DMOS-transistor outputs have sink-current capability. The serial output (SER OUT) is clocked out of the device on the falling edge of SRCK to provide additional hold time for cascaded applications. This will provide improved performance for applications where clock signals may be skewed, devices are not located near one another, or the system must tolerate electromagnetic interference.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink-current capability. Each output provides a 500-mA typical current limit at  $T_C = 25^{\circ}C$ . The current limit decreases as the junction temperature increases for additional device protection.

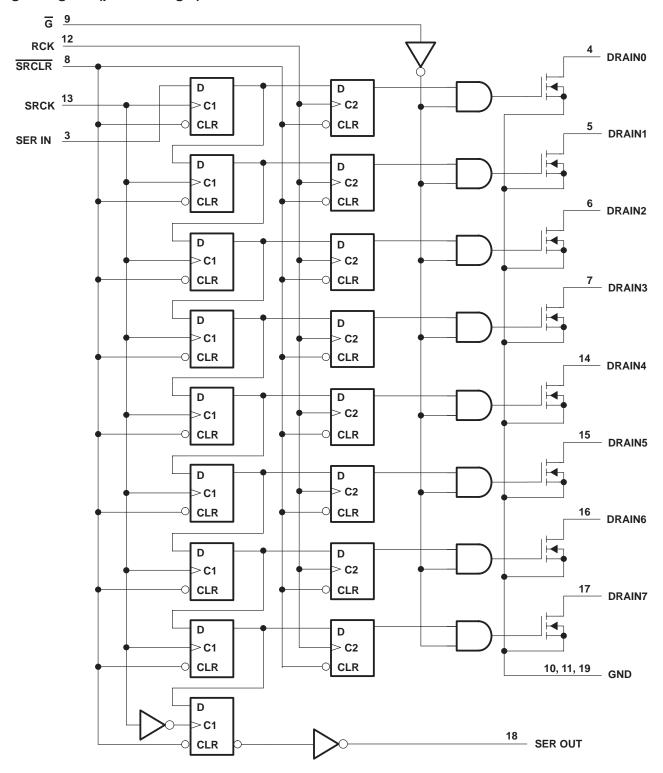
The TPIC6B596 is characterized for operation over the operating case temperature range of -40°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

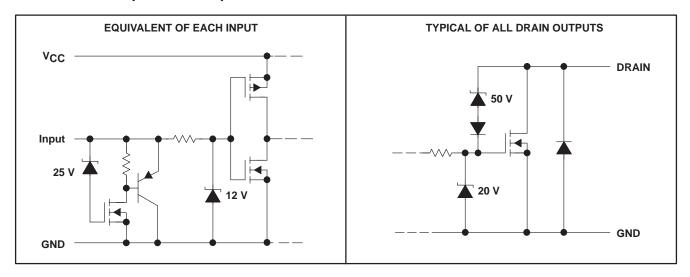


#### logic diagram (positive logic)





#### schematic of inputs and outputs



## absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) $\!\!\!\!\!\!^{\dagger}$

Logic supply voltage, V <sub>CC</sub> (see Note 1)	7 V
Logic input voltage range, V <sub>I</sub>	
Power DMOS drain-to-source voltage, V <sub>DS</sub> (see Note 2)	
Continuous source-to-drain diode anode current	
Pulsed source-to-drain diode anode current (see Note 3)	
Pulsed drain current, each output, all outputs on, I <sub>D</sub> , T <sub>C</sub> = 25°C (see Note 3)	
Continuous drain current, each output, all outputs on, $I_D$ , $T_C = 25^{\circ}C$	
Peak drain current single output, I <sub>DM</sub> ,T <sub>C</sub> = 25°C (see Note 3)	
Single-pulse avalanche energy, E <sub>AS</sub> (see Figure 4)	
Avalanche current, I <sub>AS</sub> (see Note 4)	
Continuous total dissipation	
Operating virtual junction temperature range, T <sub>J</sub>	
Operating case temperature range, T <sub>C</sub>	
Storage temperature range	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to GND.
  - 2. Each power DMOS source is internally connected to GND.
  - 3. Pulse duration  $\leq$  100  $\mu$ s and duty cycle  $\leq$  2%.
  - 4. DRAIN supply voltage = 15 V, starting junction temperature ( $T_{JS}$ ) = 25°C, L = 200 mH,  $I_{AS}$  = 0.5 A (see Figure 4).

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>C</sub> = 25°C	T <sub>C</sub> = 125°C POWER RATING
DW	1389 mW	11.1 mW/°C	278 mW
N	1050 mW	10.5 mW/°C	263 mW



#### **TPIC6B596 POWER LOGIC 8-BIT SHIFT REGISTER**

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#### recommended operating conditions

	N	IIN	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>		4.5	5.5	V
High-level input voltage, V <sub>IH</sub>	0.85	VCC		V
Low-level input voltage, V <sub>IL</sub>			0.15 V <sub>CC</sub>	V
Pulsed drain output current, $T_C = 25^{\circ}C$ , $V_{CC} = 5$ V (see Notes 3 and 5)	- 5	500	500	mA
Setup time, SER IN high before SRCK↑, t <sub>SU</sub> (see Figure 2)		15		ns
Hold time, SER IN high after SRCK↑, th (see Figure 2)		15		ns
Pulse duration, t <sub>W</sub> (see Figure 2)		40		ns
Operating case temperature, T <sub>C</sub>	-	40	125	°C

NOTES: 3. Pulse duration  $\leq$  100  $\mu$ s and duty cycle  $\leq$  2%.

5. Technique should limit  $T_J - T_C$  to 10°C maximum.

### electrical characteristics, $V_{CC}$ = 5 V, $T_{C}$ = 25°C (unless otherwise noted)

	PARAMETER	TEST COND	ITIONS	MIN	TYP	MAX	UNIT
V(BR)DSX	Drain-to-source breakdown voltage	$I_D = 1 \text{ mA}$		50			V
V <sub>SD</sub>	Source-to-drain diode forward voltage	IF = 100 mA			0.85	1	٧
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	High-level output voltage,	$I_{OH} = -20 \mu A, V_{CC} = 4.5 V$		4.4	4.49		V
VOH	SER OUT	$I_{OH} = -4 \text{ mA},  V_{CC} = 4.5 \text{ V}$		4	4.2		V
V	Low-level output voltage,	$I_{OL} = 20 \mu A$ , $V_{CC} = 4.5 V$			0.005	0.1	V
VOL	SER OUT	$I_{OL} = 4 \text{ mA},  V_{CC} = 4.5 \text{ V}$			0.3	0.5	V
lн	High-level input current	$V_{CC} = 5.5 \text{ V},  V_{I} = V_{CC}$				1	μΑ
I <sub>I</sub> L	Low-level input current	$V_{CC} = 5.5 \text{ V},  V_{I} = 0$				-1	μΑ
	Laria sumah sumant	V 55V	All outputs off		20	100	•
lcc	Logic supply current	V <sub>CC</sub> = 5.5 V	All outputs on		150	300	μΑ
ICC(FRQ)	Logic supply current at frequency	fSRCK = 5 MHz, C <sub>L</sub> = 30 pF, All outputs off, See Figures	2 and 6		0.4	5	mA
I <sub>N</sub>	Nominal current	$V_{DS(on)} = 0.5 \text{ V},$ $I_{N} = I_{D},   T_{C} = 85^{\circ}C$	See Notes 5, 6, and 7		90		mA
	Off state due in comment	$V_{DS} = 40 \text{ V},  V_{CC} = 5.5 \text{ V}$			0.1	5	^
IDSX	Off-state drain current	$V_{DS} = 40 \text{ V},  V_{CC} = 5.5 \text{ V},$	T <sub>C</sub> = 125°C		0.15	8	μΑ
		$I_D = 100 \text{ mA},  V_{CC} = 4.5 \text{ V}$			4.2	5.7	
rDS(on)	Static drain-source on-state resistance	$I_D = 100 \text{ mA},  T_C = 125^{\circ}\text{C}, \ V_{CC} = 4.5 \text{ V}$	See Notes 5 and 6 and Figures 7 and 8		6.8	9.5	Ω
		$I_D = 350 \text{ mA},  V_{CC} = 4.5 \text{ V}$			5.5	8	

NOTES: 5. Technique should limit T<sub>J</sub> – T<sub>C</sub> to 10°C maximum.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at  $T_C = 85^{\circ}C$ .



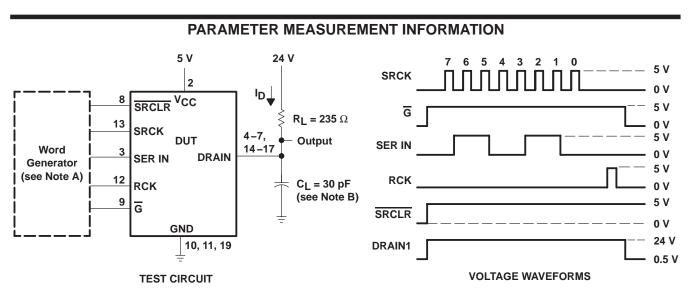
#### switching characteristics, $V_{CC} = 5 \text{ V}$ , $T_{C} = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
<sup>t</sup> PLH	Propagation delay time, low-to-high-level output from $\overline{G}$		150		ns
tPHL	Propagation delay time, high-to-low-level output from $\overline{G}$	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$	90		ns
t <sub>r</sub>	Rise time, drain output	See Figures 1, 2, and 9	200		ns
tf	Fall time, drain output		200		ns
<sup>t</sup> pd	Propagation delay time, SRCK↓ to SEROUT	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$ See Figure 2	15		ns
f(SRCK)	Serial clock frequency	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$ See Note 8		10	MHz
ta	Reverse-recovery-current rise time	$I_F = 100 \text{ mA}, \qquad di/dt = 20 \text{ A/}\mu\text{s},$	100		
t <sub>rr</sub>	Reverse-recovery time	See Notes 5 and 6 and Figure 3	300		ns

- NOTES: 5. Technique should limit T<sub>J</sub> T<sub>C</sub> to 10°C maximum.
  - 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
  - 8. This is the maximum serial clock frequency assuming cascaded operation where serial data is passed from one stage to a second stage. The clock period allows for SRCK → SEROUT propagation delay and setup time plus some timing margin.

#### thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT	
D	R <sub>θJA</sub> Thermal resistance, junction-to-ambient	DW package	All 8 outputs with equal power		90	°C/W
NθJA		N package	All 6 outputs with equal power		95	°C/VV

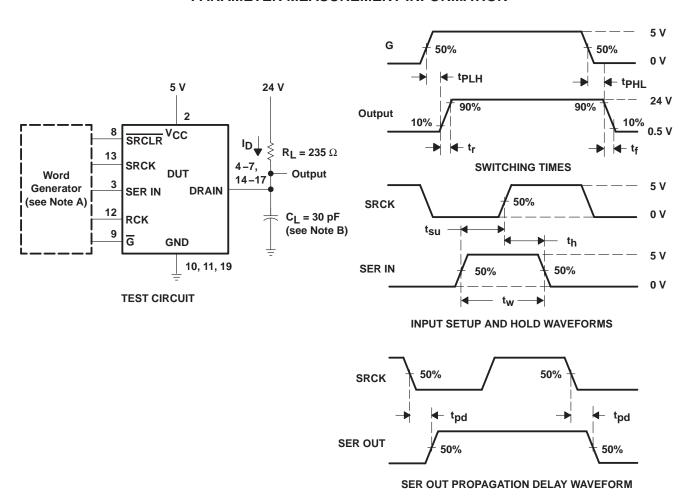


NOTES: A. The word generator has the following characteristics:  $t_{\text{f}} \le 10$  ns,  $t_{\text{f}} \le 10$  ns,  $t_{\text{W}} = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_{\text{O}} = 50~\Omega$ .

B. CL includes probe and jig capacitance.

Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

#### PARAMETER MEASUREMENT INFORMATION

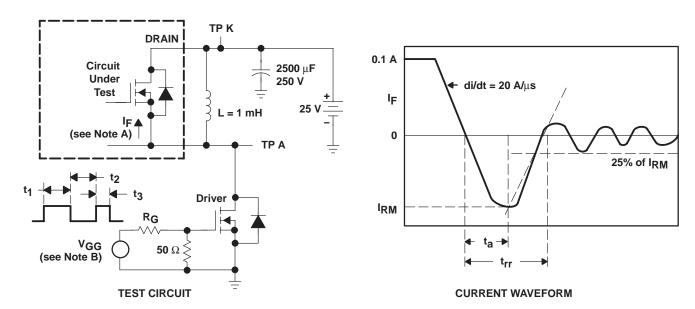


NOTES: A. The word generator has the following characteristics:  $t_{\Gamma} \le 10$  ns,  $t_{W} = 300$  ns, pulsed repetition rate (PRR) = 5 kHz,  $Z_{O} = 50~\Omega$ .

B. CL includes probe and jig capacitance.

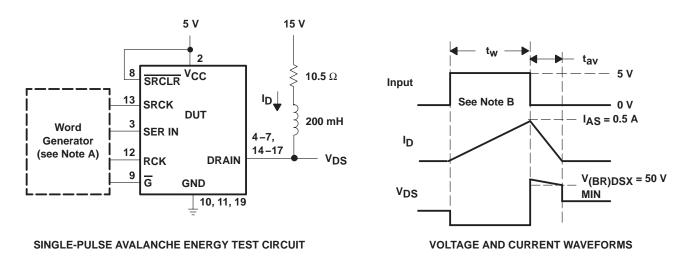
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
  - B. The  $V_{GG}$  amplitude and  $R_{G}$  are adjusted for di/dt = 20 A/ $\mu$ s. A  $V_{GG}$  double-pulse train is used to set  $I_{F}$  = 0.1 A, where  $t_{1}$  = 10  $\mu$ s,  $t_{2}$  = 7  $\mu$ s, and  $t_{3}$  = 3  $\mu$ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode

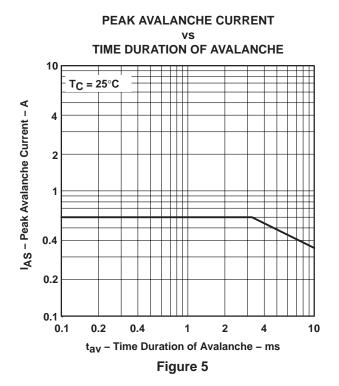


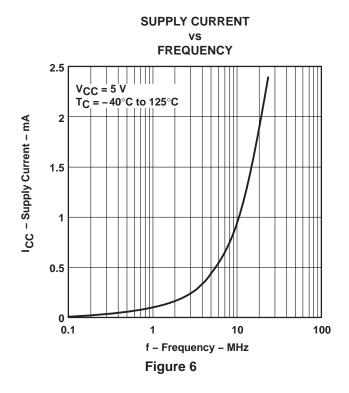
- NOTES: A. The word generator has the following characteristics:  $t_{\Gamma} \le 10$  ns,  $t_{f} \le 10$  ns,  $t_{O} = 50 \Omega$ .
  - B. Input pulse duration,  $t_W$ , is increased until peak current  $I_{AS} = 0.5$  A. Energy test level is defined as  $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30$  mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms



#### **TYPICAL CHARACTERISTICS**





# DRAIN-TO-SOURCE ON-STATE RESISTANCE vs

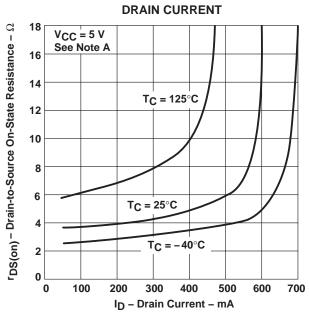
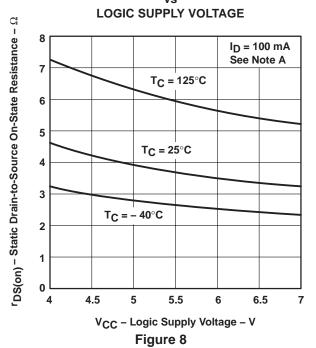


Figure 7

## STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE vs



SLIS095A - MARCH 2000 - REVISED MAY 2005

#### **TYPICAL CHARACTERISTICS**

# SWITCHING TIME vs CASE TEMPERATURE

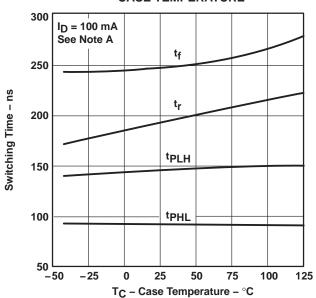
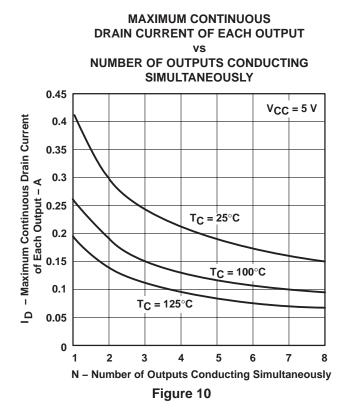
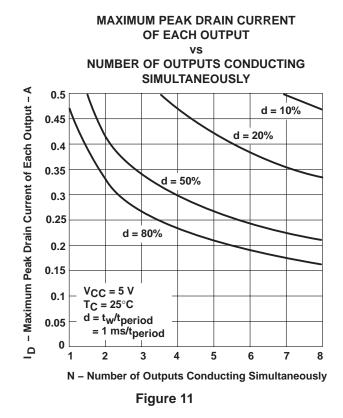


Figure 9

NOTE A: Technique should limit  $T_J - T_C$  to 10°C maximum.

#### THERMAL INFORMATION





**Revision History** 

DATE	REV	PAGE	SECTION	DESCRIPTION				
5/18/05	Α	5	Figure 1	Changed SRCLR timing diagram				
3/2000	*			Original reversion				

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.





23-Apr-2012

#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
TPIC6B596DW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B596DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B596DWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B596DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B596N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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#### PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6B596DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 4-Jan-2013



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6B596DWR	SOIC	DW	20	2000	367.0	367.0	45.0

#### N (R-PDIP-T\*\*)

#### PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

#### PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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